

**Solid State
Micro
Technology**
for Music

ADVANCE
INFORMATION

**SSM
2012**

\$ 2.50

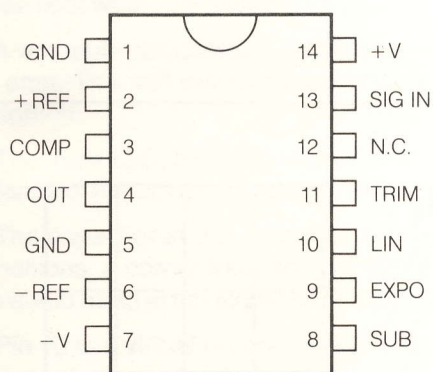
VOLTAGE CONTROLLED AMPLIFIER*

DESCRIPTION

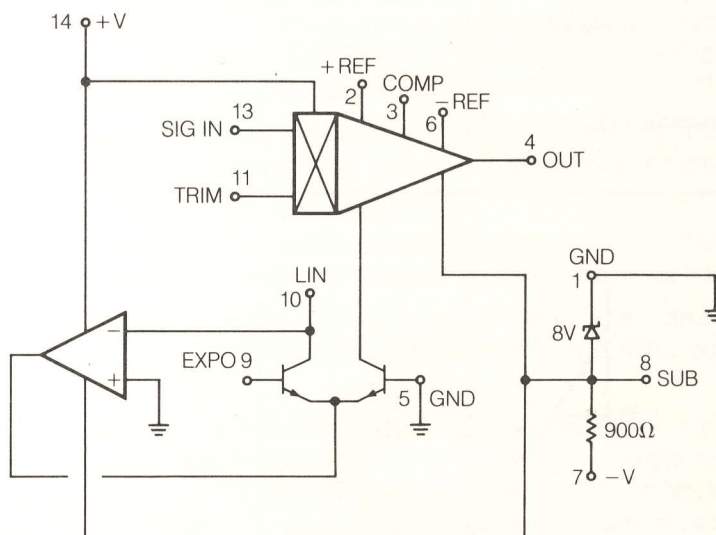
The SSM 2012 is a low cost, high performance linear-antilog voltage controlled amplifier with full class A performance. The device has a 100 dB signal to noise figure at 0.01% THD. The current inputs and outputs make possible wide bandwidth, easy signal summing, and minimum external component count. Inherently low control feedthrough and 2nd harmonic distortion make trimming unnecessary for most applications.* In addition, the 2012 has more than 12dB of headroom at the rated specifications and can be configured to give up to 40dB of gain.

FEATURES

- 100dB Signal/Noise (20Hz-20KHz)
- 0.01% THD
- 0.025% IMD
- 12dB of Headroom (at rated specs.)
- 100KHz Bandwidth
- Linear and Exponential Control Inputs
- 40dB Gain Capability
- Low Cost
- Full Class A Performance
- Minimum External Component Count
- Current Input
- Current Output
- -40dB Control Feedthrough (untrimmed)
- No Trimming Required for Most Applications



PIN OUT (TOP VIEW)



BLOCK DIAGRAM

SPECIFICATIONS***OPERATING TEMPERATURE**

- 10°C to + 55°C

STORAGE TEMPERATURE

- 55°C to + 125°C

Specification* @ $V_s = \pm 15V$ and $T_A = 25^\circ C$

PARAMETER	MIN	TYP	MAX	UNITS	CONDITIONS
Positive Supply Voltage	+ 12	+ 15	+ 18	V	
Negative Supply Voltage ¹	- 7.6	- 8.2	- 8.7	V	
Positive Supply Current	6.5	8.7	11.5	mA	
Negative Supply Current	6.5	8.7	11.5	mA	
Negative Supply Bias Resistor (pin 7 to pin 8)	675	900	1170	Ω	
Expo Input Bias	0.25	0.5	1.3	μA	$V_e = GND, I_L = + 100\mu A$
Expo Control Sensitivity		- 10		mV/dB	at pin 9
Linear Input Bias	0.25	0.5	1.3	μA	$V_e = 300mV, I_L = 0$
Linear Control Sensitivity	0.98	1	1.02	%/ μA	
Trim Input Resistance to GND	9	12	15.6	Ω	
Current Gain	0.95	1.0	1.05		$V_e = GND, I_L = + 100\mu A$
Current Output Offset (untrimmed)	- 5	0	+ 5	μA	$V_e = GND, I_L = + 100\mu A$
Output Leakage	- 10	0	+ 10	nA	$V_e = + 600mV, I_L = + 100\mu A$
Max Available Output Current	- 800	0	+ 800	μA	$V_e = GND, I_L = + 100\mu A$
Current Bandwidth (3dB)		300		KHz	$V_e = GND, I_L = + 100\mu A$
Signal Feedthrough		- 105		dB	$I_L = 0$
Signal to Noise (20Hz-20KHz)		- 98		dB	$V_e = GND, I_L = 100\mu A$
THD (untrimmed)		0.025		%	$V_e = GND, I_L = 100\mu A$
THD (trimmed)		0.01		%	$V_e = GND, I_L = 100\mu A$
IMD (untrimmed)		0.075		%	$V_e = GND, I_L = 100\mu A$
IMD (trimmed)		0.03		%	$V_e = GND, I_L = 100\mu A$

*Final Specifications may be subject to change.

1) Measured at pin 8, pin 7 = - 15V.

